Amplifier Transistors

NPN Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

` ' ' '		,	
Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	75	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

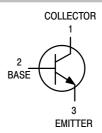
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

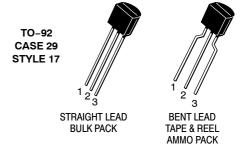
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



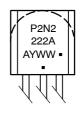
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
P2N2222AG	TO-92 (Pb-Free)	5000 Units/Bulk
P2N2222ARL1G	TO-92 (Pb-Free)	2000/Tape & Ammo

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u> </u>			II.
Collector – Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	40	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	75	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	6.0	-	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	I _{CEX}	_	10	nAdc
Collector Cutoff Current	I _{CBO}	- -	0.01 10	μAdc
Emitter Cutoff Current $(V_{EB} = 3.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	10	nAdc
Collector Cutoff Current (V _{CE} = 10 V)	I _{CEO}	-	10	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	I _{BEX}	-	20	nAdc
ON CHARACTERISTICS		•	•	
DC Current Gain	h _{FE}	35 50 75 35 100 50 40	- - - 300 -	-
Collector – Emitter Saturation Voltage (Note 1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	V _{CE(sat)}	- -	0.3 1.0	Vdc
Base – Emitter Saturation Voltage (Note 1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	V _{BE(sat)}	0.6	1.2 2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u> </u>	ļ	ļ	ļ.
Current – Gain – Bandwidth Product (Note 2) (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)C	f _T	300	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	25	pF
Input Impedance $ \begin{array}{l} \text{(I}_C=1.0 \text{ mAdc, V}_{CE}=10 \text{ Vdc, f}=1.0 \text{ kHz)} \\ \text{(I}_C=10 \text{ mAdc, V}_{CE}=10 \text{ Vdc, f}=1.0 \text{ kHz)} \end{array} $	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
Small–Signal Current Gain $ \begin{aligned} &(I_C=1.0 \text{ mAdc, V}_{CE}=10 \text{ Vdc, f}=1.0 \text{ kHz}) \\ &(I_C=10 \text{ mAdc, V}_{CE}=10 \text{ Vdc, f}=1.0 \text{ kHz}) \end{aligned} $	h _{fe}	50 75	300 375	_
Output Admittance $ \begin{aligned} \text{(I}_{C} &= 1.0 \text{ mAdc, V}_{CE} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \\ \text{(I}_{C} &= 10 \text{ mAdc, V}_{CE} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \end{aligned} $	h _{oe}	5.0 25	35 200	μMhos
Collector Base Time Constant ($I_E = 20 \text{ mAdc}, V_{CB} = 20 \text{ Vdc}, f = 31.8 \text{ MHz}$)	rb′C _c	-	150	ps
Noise Figure $(I_C = 100 \; \mu Adc, V_{CE} = 10 \; Vdc, R_S = 1.0 \; k\Omega, f = 1.0 \; kHz)$	N _F	_	4.0	dB

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%. 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -2.0 \text{ Vdc},$	t _d	-	10	ns
Rise Time	$I_C = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc}) \text{ (Figure 1)}$	t _r	-	25	ns
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc,	t _s	-	225	ns
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$ (Figure 2)	t _f	-	60	ns

SWITCHING TIME EQUIVALENT TEST CIRCUITS

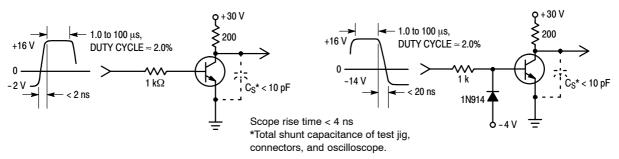


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

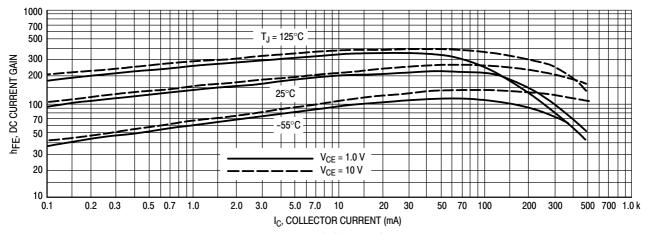


Figure 3. DC Current Gain

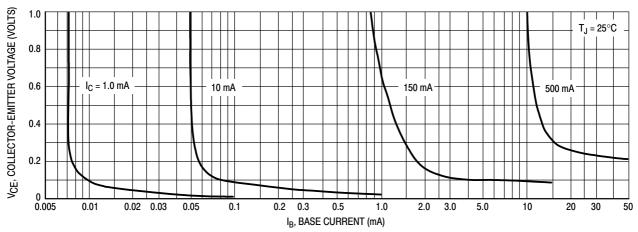


Figure 4. Collector Saturation Region

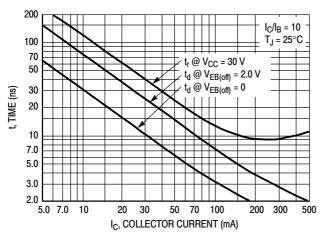


Figure 5. Turn - On Time

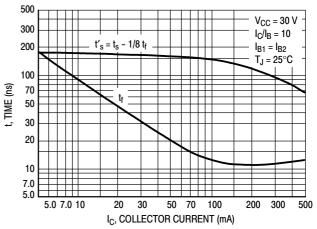


Figure 6. Turn - Off Time

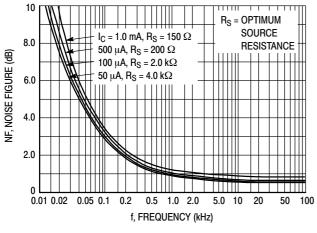


Figure 7. Frequency Effects

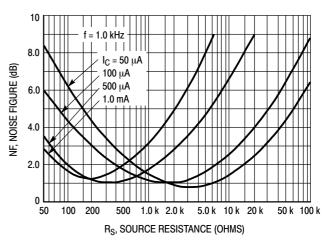


Figure 8. Source Resistance Effects

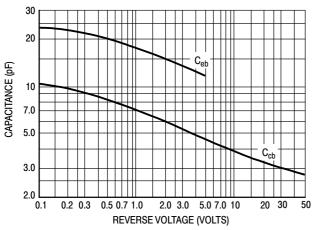
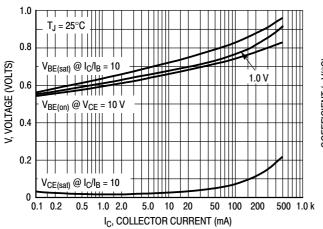
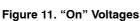


Figure 9. Capacitances

Figure 10. Current-Gain Bandwidth Product





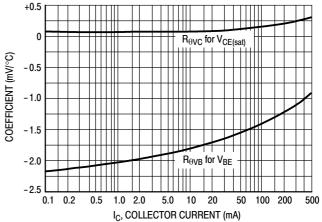
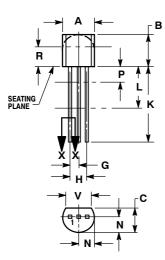


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



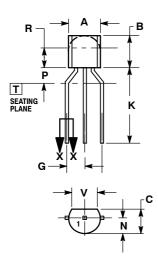
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

 4. LEAD DIMENSION IS UNCONTROLLED IN P

- AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 17: PIN 1. COLLECTOR BASE

ON Semiconductor and war registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent—Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different application and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products are not designed, intended, or authorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportuni

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA **Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative